

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

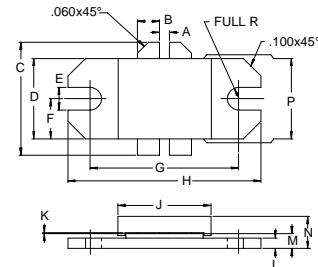
The **ASI CBSL60B** is Designed for Class AB, Cellular Base Station Applications up to 960 MHz.

**FEATURES:**

- Internal Input/Output Matching Networks
- $P_G = 8.5$  dB at 60 W/960 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	8.0 A
$V_{CBO}$	60 V
$V_{CEO}$	28 V
$V_{EBO}$	3.5 V
$P_{DISS}$	146 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.2 °C/W

**PACKAGE STYLE .450 BAL FLG (A)**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C	.785 / 19.94	
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N	.195 / 4.95	
P	.445 / 11.30	.455 / 11.56

**ORDER CODE: ASI10584**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 100$ mA	60			V
$BV_{CEO}$	$I_C = 100$ mA	28			V
$BV_{EBO}$	$I_E = 20$ mA	3.5			V
$I_{CEO}$	$V_{CE} = 25$ V			30	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 3.0$ A	25		80	---
$P_G$	$V_{CC} = 26$ V $I_{CQ} = 2 \times 200$ mA $f = 960$ MHz $P_{OUT} = 60$ W	8.5			dB
$VSRW$	$V_{CC} = 26$ V $f = 960$ MHz	5:1			---